KSN3350Q

20V Dual N-Channel MOSFET

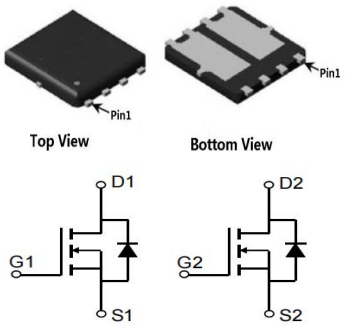
General Description

The KSN3350Q combines advanced trench MOSFET technology with a low resistance package to provide extremely low R_{DS}(ON). This device is ideal for load switch and battery protection applications.

Product Summary

V_{DS} (V)	R_{DS}(on) (mΩ)	I_D (A)
20	3.5 at V_{GS} = 4.5 V	58
	4.5 at V_{GS} = 2.5 V	35

PDFN3*3 Pin Configuration



Features

- Small package volume
- ESD protection
- Green products

Applications

- ESD Protected
- Li-Battery Protection

100% UIS TESTED!
100% ΔVds TESTED!

Absolute Maximum Ratings T_C=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D	Drain Current – Continuous (T_C=25℃)	58	A
	Drain Current – Continuous (T_C=100℃)	22	A
I_{DM}	Drain Current – Pulsed[1]	130	A
P_D	Power Dissipation (T_C=25℃)	19	W
	Power Dissipation – Derate above 25℃	11	W/℃
T_{STG}	Storage Temperature Range	-50 to 150	℃
T_J	Operating Junction Temperature Range	-50 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	1.72	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	20	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.01	---	V/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=20V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=20V , V_{GS}=0V , T_J=125℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±12V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=4.5V , I_D=10A	---	3.5	4.1	mΩ
		V_{GS}=2.5V , I_D=5A	---	4.5	5.5	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	0.5	0.8	1.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	0.8	---	mV/℃
gfs	Forward Transconductance	V_{DS}=5V , I_S=10A	---	40	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[2,3]	V_{DS}=10V , V_{GS}=4.5V , I_D=3A	---	31.6	42	nC
Q_{gs}	Gate-Source Charge[2,3]		---	3.0	5.3	
Q_{gd}	Gate-Drain Charge[2,3]		---	10.1	16.6	
$T_{d(on)}$	Turn-On Delay Time[2,3]	V_{DS}=10V , V_{GS}=4.5V , R_G=3.3 Ω I_D=3A	---	6.3	9	ns
T_r	Rise Time[2,3]		---	19.5	26	
$T_{d(off)}$	Turn-Off Delay Time[2,3]		---	62.6	80	
T_f	Fall Time[2,3]		---	18.3	30	
C_{iss}	Input Capacitance	V_{DS}=10V , V_{GS}=0V , F=1MHz	---	2265	2560	pF
C_{oss}	Output Capacitance		---	283	346	
C_{rss}	Reverse Transfer Capacitance		---	216	275	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	50	A
I_{SM}	Pulsed Source Current		---	---	100	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.20	V

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

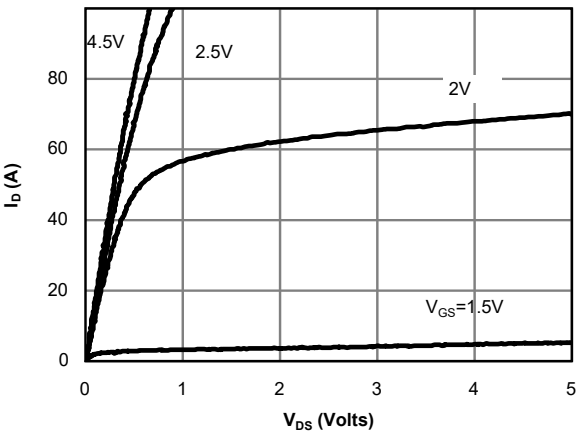


Fig 1: On-Region Characteristics (Note E)

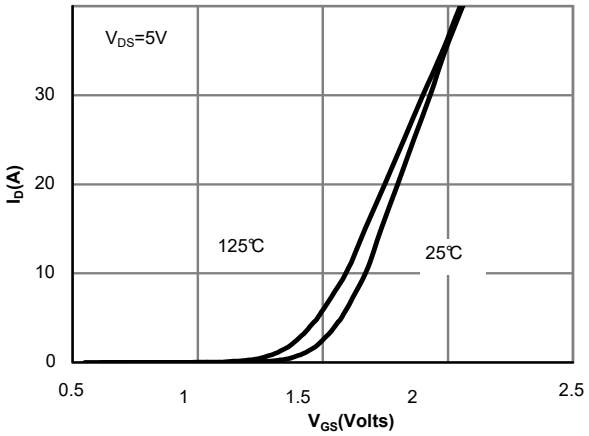


Figure 2: Transfer Characteristics (Note E)

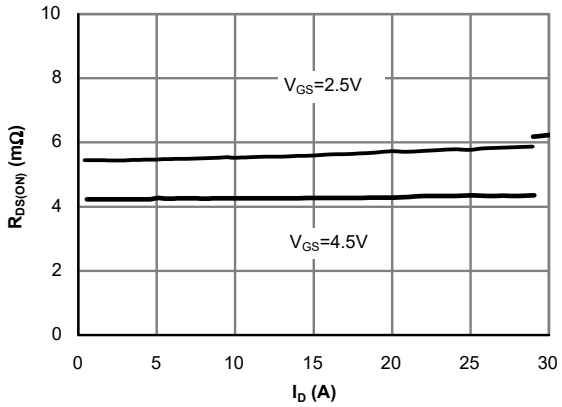


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

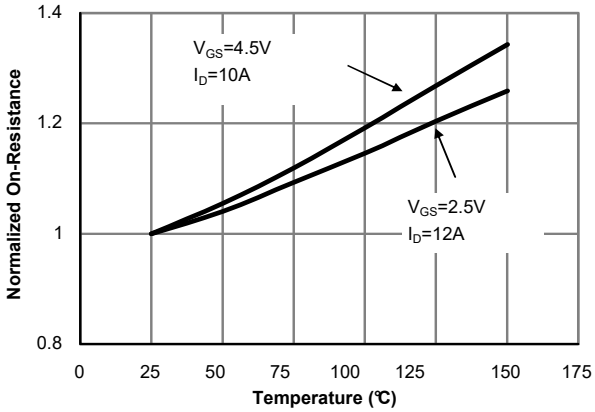


Figure 4: On-Resistance vs. Junction Temperature (Note E)

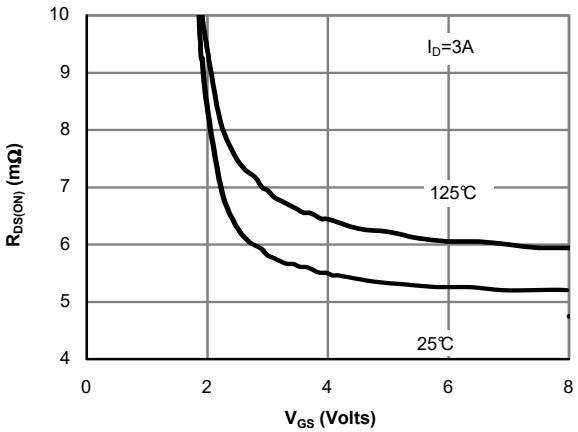


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

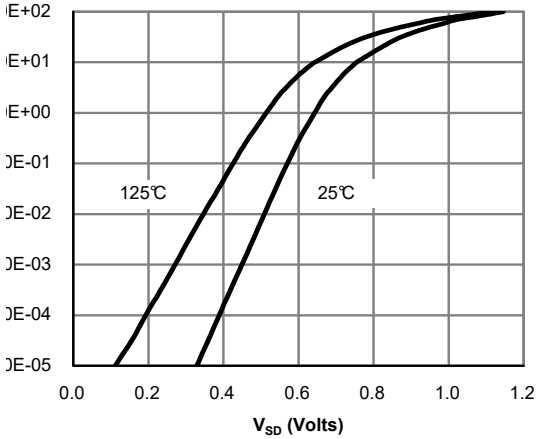


Figure 6: Body-Diode Characteristics (Note E)

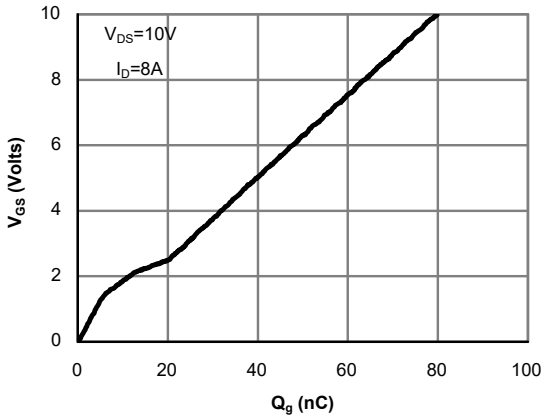


Figure 7: Gate-Charge Characteristics

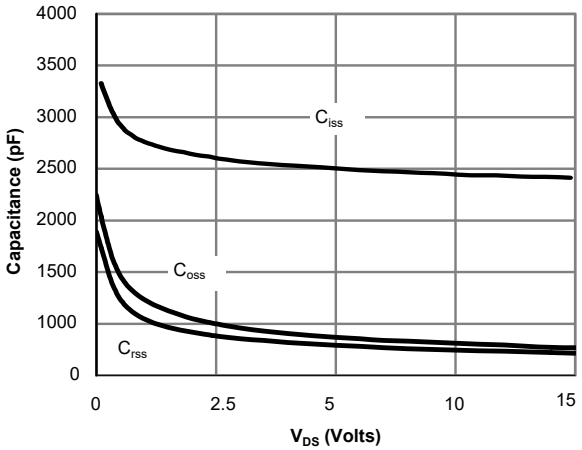


Figure 8: Capacitance Characteristics

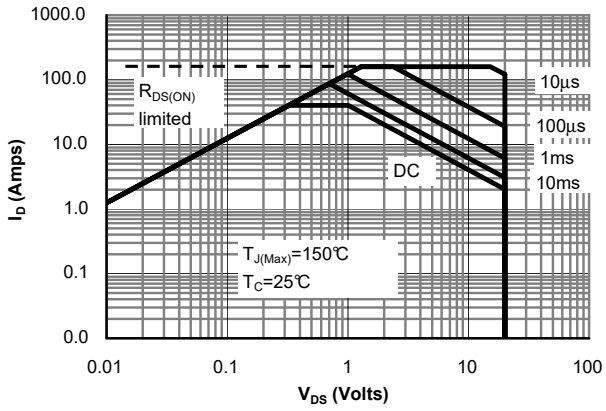


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

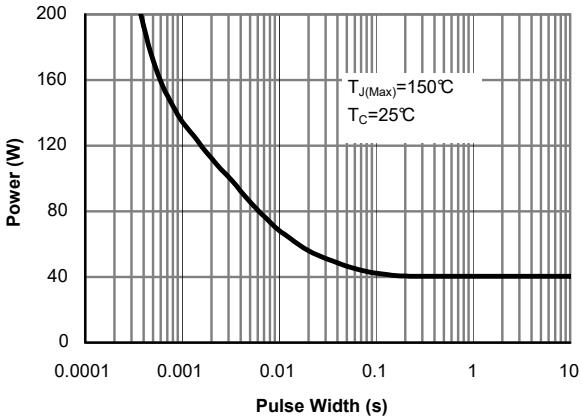


Figure 10: Single Pulse Power Rating ction-to-Case (Note F)

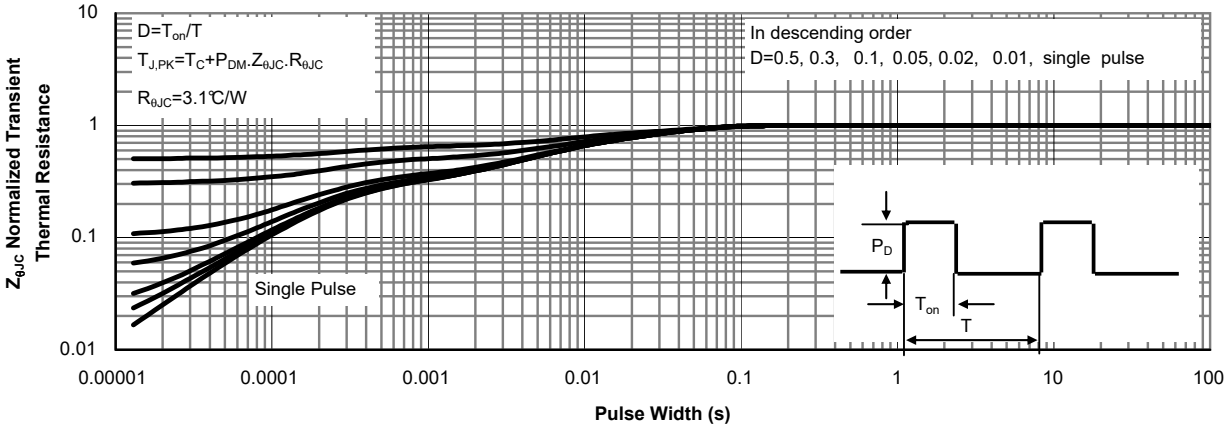


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

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